AMENDMENTS TO THE SPECIFICATION

- Please replace the Cross-Reference to Related Application(s) section as follows:

CROSS-REFERENCE TO RELATED APPLICATION

This is a ~~continuation~~ divisional of co-pending application serial number ~~09/164,421~~10/226,520, filed August 22, 2002, which is a continuation of 09/874,175 filed June 4, 2001, since issued as U.S. Patent 6,469,385 B1.

- Please replace the paragraph, which begins on page 4, line 27, with the following amended paragraph:

An integrated circuit ~~and manufacturing method therefor~~ is provided having a semiconductor substrate with a semiconductor device. A dielectric layer formed over the semiconductor substrate has an opening provided therein. The dielectric layer is of non-barrier dielectric material capable of being changed into a barrier dielectric material. The dielectric layer around the opening is changed into the barrier dielectric material and the conductor core material is deposited to fill the opening. The conductor core is processed to form a channel for the integrated circuit. This allows a selective conversion of dielectric materials with no diffusion barrier properties to be converted into good barrier materials which allows larger channels and shrinkage of the integrated circuit.

Please replace the Abstract section as follows:

An integrated circuit ~~and manufacturing method therefor~~ is provided having a semiconductor substrate with a semiconductor device. A dielectric layer formed over the semiconductor substrate has an opening provided therein. The dielectric layer is of non-barrier dielectric material capable of being changed into a barrier dielectric material. The dielectric layer around the opening is changed into the barrier dielectric material and the conductor core material is deposited to fill the opening. The conductor core is processed to form a channel for the integrated circuit. This allows a selective conversion of dielectric materials with no diffusion barrier properties to be converted into good barrier materials which allows larger channels and shrinkage of the integrated circuit.